

# Product data sheet

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## Features

- Solid-state silicon-avalanche technology
- Low operating and clamping voltage
- Up to four I/O Lines of Protection
- Ultra low capacitance: 0.5pF typical(I/O to I/O)
- Low Leakage
- Low operating voltage:5V
- Flow-Through design

# IEC COMPATIBILITY (EN61000-4)

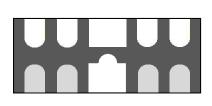
- IEC 61000-4-2 (ESD) ±15kV (air), ±8kV (contact)
- IEC 61000-4-4 (EFT) 40A (5/50ns)
- IEC 61000-4-5 (Lightning) 5A (8/20µs)

## **Mechanical Characteristics**

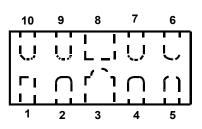
- DFN2510-10
- Molding compound flammability rating: UL 94V-0
- Marking: Marking Code
- Packaging: Tape and Reel
- RoHS/WEEE Compliant

# Applications

- Digital Visual Interface(DVI)
- MDDI Ports
- DisplayPortTM Interface
- PCI Express
- High Definition Multi-Media Interface(HDMI)
- eSATA Interfaces

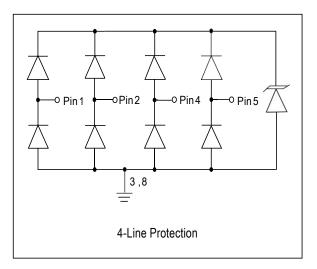


## Schematic & PIN Configuration



Pin	Identificaion	
1,2,4,5	Input Lines	
6,7,9,10	Output Lines (No Internal Connection)	
3,8	Ground	

# **Circuit Diagram**





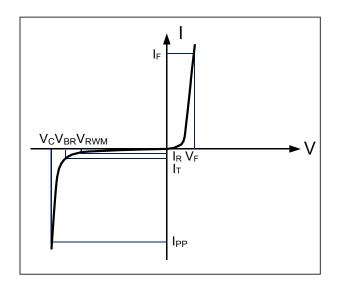
Semiconductor Compiance

# Absolute Maximum Rating

Rating	Symbol	Value	Units
Peak Pulse Power ( $t_p = 8/20 \mu s$ )	P <sub>PP</sub>	150	Watts
Peak Pulse Current ( t <sub>p</sub> =8/20µs )	I <sub>pp</sub>	5	А
ESD per IEC 61000-4-2(Air) ESD per IEC 61000-4-2(contact)	V <sub>ESD</sub>	+/-17 +/-12	kV
Operating Temperature	TJ	-55 to + 125	°C
Storage Temperature	T <sub>STG</sub>	-55 to +150	°C

# Electrical Parameters (T=25°C)

Symbol	Parameter	
Ірр	Maximum Reverse Peak Pulse Current	
Vc	Clamping Voltage @ IPP	
VRWM	Working Peak Reverse Voltage	
IR	Maximum Reverse Leakage Current @ VRWM	
VBR	Breakdown Voltage @ I⊤	
Ιτ	Test Current	
IF	Forward Current	
VF	Forward Voltage @ I⊧	



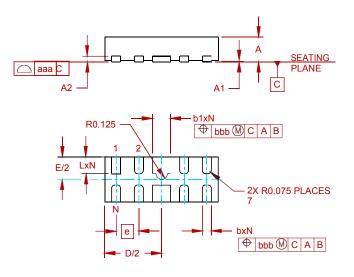
# **Electrical Characteristics**

Parameter	Symbol	Conditions	Minimum	Typical	Maximum	Units
Reverse Stand-Off Voltage	V <sub>RWM</sub>	Any I/O pin to ground			5.0	V
Reverse Breakdown Voltage	V <sub>BR</sub>	I <sub>t</sub> = 1mA Any I/O pin to ground	6.0			V
Reverse Leakage Current	I <sub>R</sub>	V <sub>RWM</sub> = 5V, T=25°C Any I/O pin to ground			1	μA
Clamping Voltage	Vc	l <sub>pp</sub> =5A, t <sub>p</sub> =8/20µs Any I/O pin to ground			15	V
		V <sub>R</sub> = 0V, f = 1MHz I/O pin to GND			0.8	pF
Junction Capacitance	Cj	V <sub>R</sub> = 0V, f = 1MHz Between I/O pins		0.3		pF

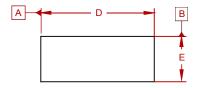


ESD5304D-MS Semiconductor Compiance

### PACKAGE MECHANICAL DATA

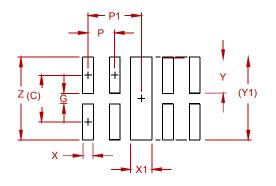


Dimensions in millimeters



DIMENSI ONS						
DIM		MILLIN	MILLIMETERS			
DIN	MIN	NOM	MAX	MIN	NOM	MAX
Α	.020	.023	.026	0.50	0.58	0.65
A1	0.00	.001	.002	0.00	0.03	0.05
A2	(.005)		(0	).13)		
b	.006	.008	.010	0.15	0.20	0.25
b1	.014	.016	.018	0.35	0.40	0.45
D	.094	.098	.102	2.40	2.50	2.60
E	.035	.039	.043	0.90	1.00	1.10
е	.020 BSC		0.5	BSC		
L	.012	.015	.017	0.30	0.38	0.425
N	8		8			
aaa	.003			0.08		
bbb	.004		0.10			

#### **Suggested Pad Layout**



	DIMENSIONS			
DIM	INCHES	MILLIMETERS		
С	(.034)	(0.875)		
G	.008	0.20		
Р	.020	0.50		
P1	.039	1.00		
Х	.008	0.20		
X1	.016	0.40		
Y	.027	0.675		
Y1	(.061)	(1.55)		
Z	.061	1.55		

#### NOTES:

CONTROLLING DIMENSIONS ARE IN MILLIMETERS (ANGLES IN DEGREES). THIS LAND PATTERN IS FOR REFERENCE PURPOSES ONLY. CONSULT YOUR MANUFACTURING GROUP TO ENSURE YOUR COMPANY'S MANUFACTURING GUIDELINES ARE MET.

#### **REEL SPECIFICATION**

P/N	PKG	QTY
ESD5304D-MS	DFN2510-10	3000



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